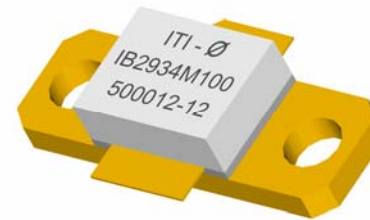


S-Band Radar Transistor

The high power pulsed radar transistor device part number IB2934M100 is designed for S-Band radar systems operating over the instantaneous bandwidth of 2.9-3.4 GHz. While operating in class C mode this common base device supplies a minimum of 100 watts of peak pulse power under the conditions of 100 μ s pulse width and 10% duty cycle. All devices are 100% screened for large signal RF parameters. Excellent spectral stability into output mismatch over a broad input power range make it ideal for use in reliable high power solid state transmitters. The test fixture includes a passive amplitude sloping network to insure that the device is not overdriven as the operating frequency decreases.



Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Unmatched Thermal Reliability

RF Test Fixture

- Broadband
- Matched to 50 Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed
- Micro-strip structure on soft pc board with dielectric constant 10.2

US Patent Number

- US 8344809B2

PRELIMINARY DATA

PRELIMINARY DATA

PRELIMINARY DATA

General Information	Freq (GHz)	Po (W)	IRL (dB)	Pin (W)	Droop (dB)	Gain (dB)	\square G (dB)	Nc (%)	Pdiss (W)
Device: D1479-1	2.90	100	10	15.1	0.10	9.3	0.76	52	103
Pulse Width = 100us									
Duty Factor = 10%	3.15	100	16	14.6	0.15	10.0	--	46	126
Vcc = 36V									
RFTF # ITI 684	3.40	100	18	18.0	0.15	9.2	--	47	124

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	70	V	$V_{BE}=0V$.
BD	Emitter-Base Voltage	V_{EBO}	--	3.5	V	--
BD	Storage Temperature Range	T_{STG}	-55	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.50	°C/W	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ C$, $P_{OUT}=100W$, $F=F3$.
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification.
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071.6, Test Condition C.
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

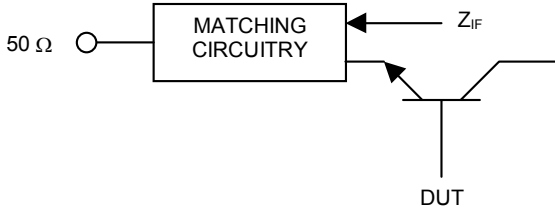
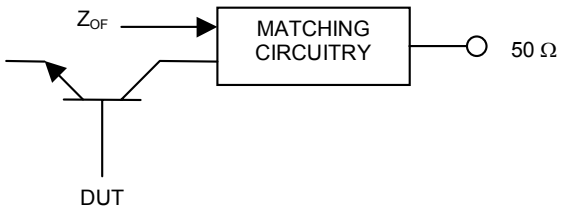
Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	70	--	V	$I_C=20mA$, $V_{BE}=0V$, $T_F=25\pm5^\circ C$.
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	3.0	mA	$V_{CE}=30V$, $V_{BE}=0V$, $T_F=25\pm5^\circ C$.
100%	DC Current Gain	H_{FE}	10	150	--	$V_{CE}=5V$, $I_C=0.1A$, $T_F=25\pm5^\circ C$.

RF ELECTRICAL CHARACTERISTICS

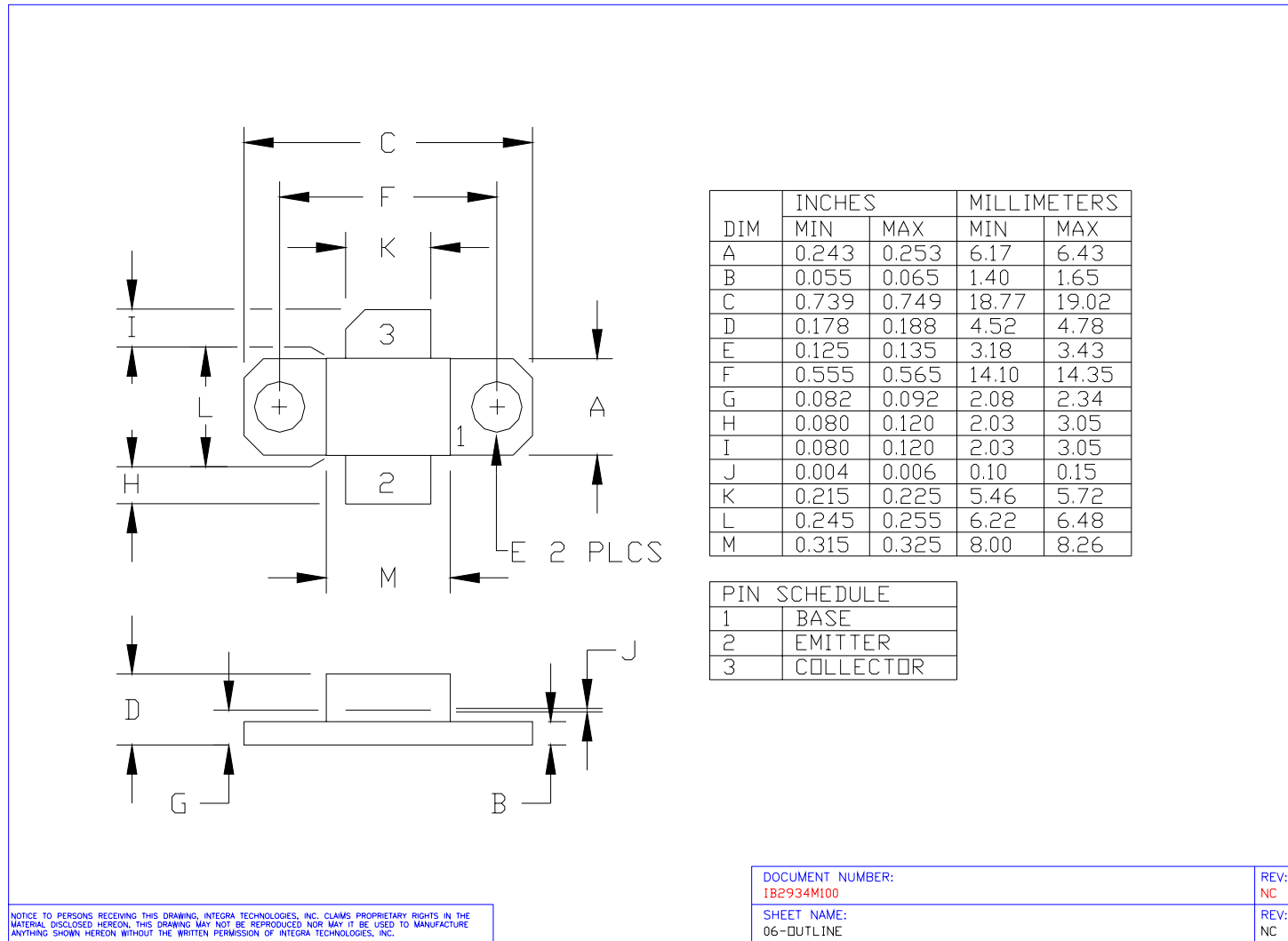
Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	9	--	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$
100%	Power Gain	G	7.5	--	W	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$
100%	Collector Efficiency (P_{OUT}/V_{CC})	N_C	40	--	%	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$
100%	Intra-Pulse Amplitude Droop	D	0.0	-1.0	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$
100%	Power Gain Flatness = ($G_{MAX} - G_{MIN}$)	ΔG	--	1.5	dB	Calculate from Power Gain at each frequency F.
100%	Delta Insertion Phase Variation	d-IP	-20	+20	Deg	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$
100%	Stability into 1.5:1 VSWR	VSWR-S	--	--	--	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$ Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse. All non-harmonically related signals must be at least -65 dBc.
BD	Pulse Risetime	RT	--	100	ns	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_O=100W, F=F1, F2, F3.$ Measure between 10% and 90% detected power points.
Note	V1 = 36V; PW1 = 100us; DF1 = 10%; F1 = 2.9 GHz, F2 = 3.15 GHz, F3 = 3.4 GHz.					
Note	T_F = Device flange temperature.					
Note	Screen 'BD' = parameter qualified By Design.					

RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

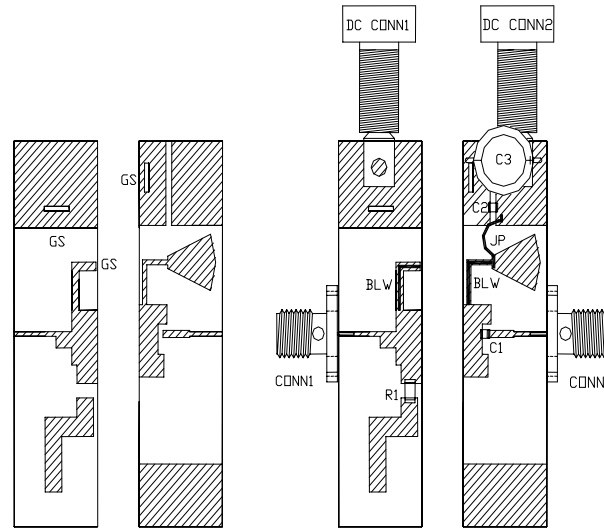
Frequency (MHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
2.90	3.0 - j3.9	3.0 - j6.0
3.15	2.7 - j3.6	2.7 - j5.7
3.40	1.5 - j2.7	1.9 - j5.0

Impedance Definition		
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PACKAGE DIMENSIONAL OUTLINE DRAWING



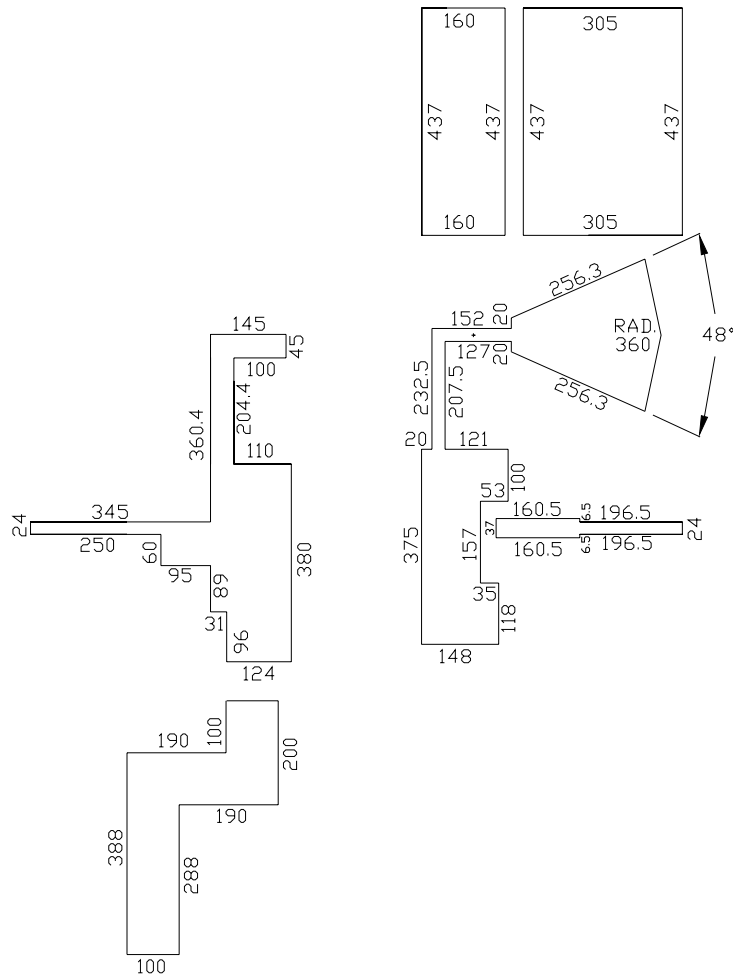
BROADBAND RF TEST FIXTURE



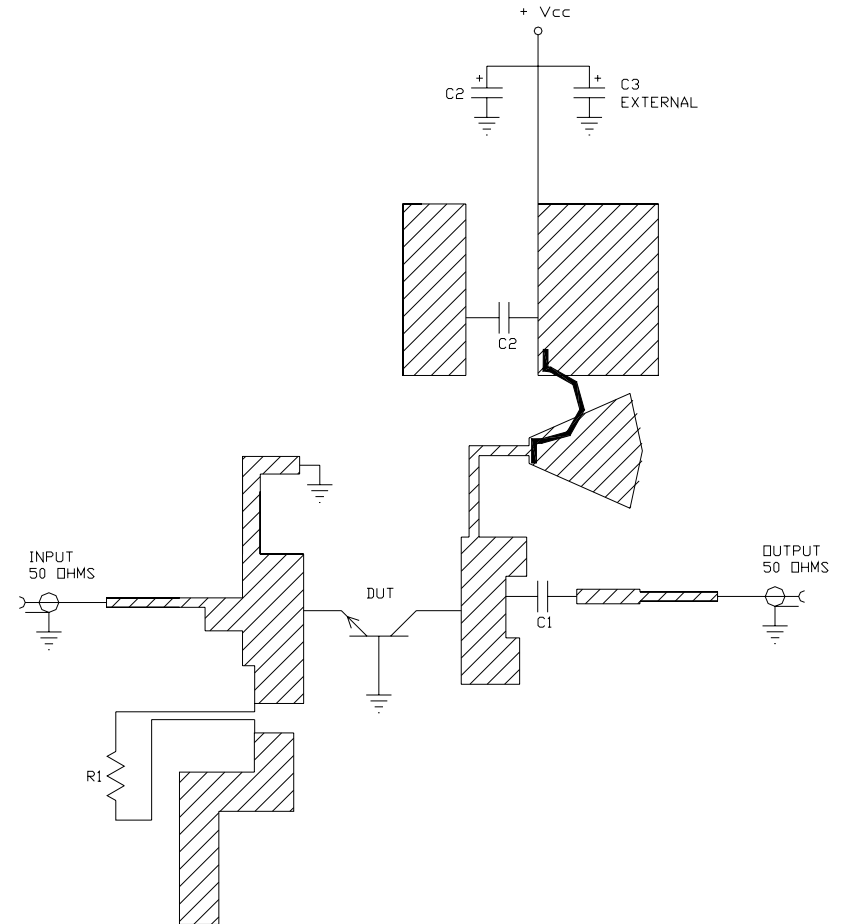
COMPONENT	DESCRIPTION
DUT	TRANSISTOR #IB2934M100, MOUNT HARD TO THE RIGHT
PC BOARD	ROGERS #6010.2LM, TH=0.025", 1E/1E
C1,C2	CHIP CAPACITOR, TYPE ATC100A, 39 pF
C3	ELECTROLYTIC CAPACITOR, 68uF / 63V
C4 - NOT SHOWN	ELECTROLYTIC CAPACITOR, 2200uF / 63V
GS	GROUND SHIM, COPPER, TH=0.001"
CONN1, CONN2	SMA CONNECTOR, TYPE DS #2052-5636-02
INPUT PC BOARD CARRIER	2 INCH BRASS - 01
OUTPUT PC BOARD CARRIER	2 INCH BRASS - 01
TRANSISTOR CARRIER	2 INCH COPPER - 01
TRANSISTOR CLAMP	NDRYL CLAMP -01
HEATSINK	2 INCH HEATSINK - 09
DC CONN1	BANANA JACK, BLACK
DC CONN2	BANANA JACK, RED
BLW	BIAS LINE WIRE - COPPER - 0.022" DIA TYPICAL
R1	CHIP RESISTOR, 100 OHM, 5%, MSI # WA57PS-1000-J-NS62
JP	JUMPER WIRE
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

ASSEMBLY AND PARTS LIST

BROADBAND RF TEST FIXTURE



CIRCUIT DIMENSIONS IN MILS (1 MIL = 0.001")



ELECTRICAL SCHEMATIC

DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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